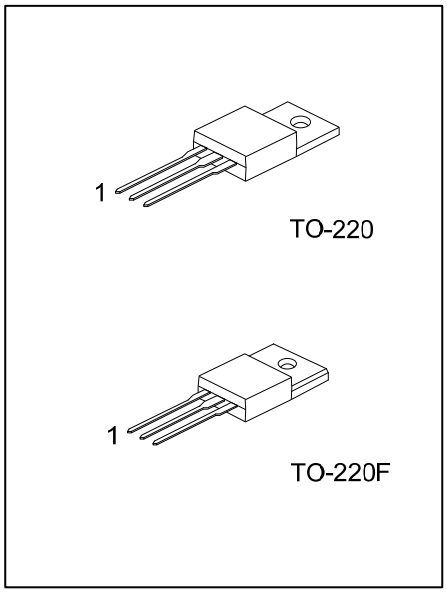
MGBR10L200C

DIODE

DUAL MOS GATED BARRIER RECTIFIER



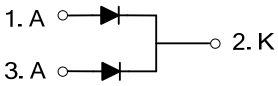
■ DESCRIPTION

The UTC **MGBR10L200C** is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

■ FEATURES

* Low forward voltage drop
* High switching speed

■ SYMBOL



■ ORDERING INFORMATION

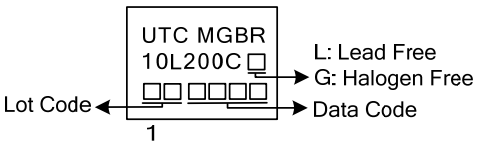
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
MGBR10L200CL-TA3-T	MGBR10L200CG-TA3-T	TO-220	A	K	A	Tube
MGBR10L200CL-TF3-T	MGBR10L200CG-TF3-T	TO-220F	A	K	A	Tube

Note: Pin Assignment: A: Anode K: Common Cathode

MGBR10L200CG-TA3-T

(1)Packing Type	(1) T: Tube
(2)Package Type	(2) TA3: TO-220, TF3: TO-220F
(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T_A=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		V_{RM}	200	V
Working Peak Reverse Voltage		V_{RWM}	200	V
Peak Repetitive Reverse Voltage		V_{RRM}	200	V
Average Rectified Output Current Per Device	Per Leg	I_O	5	A
	Total		10	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I_{FSM}	110	A
Operating Junction Temperature		T_J	-65 ~ +150	°C
Storage Temperature		T_{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS (PER LEG)

PARAMETER		SYMBOL	RATINGS	UNIT
Typical Thermal Resistance	TO-220	θ_{JC}	2	°C/W
	TO-220F		4	°C/W

■ ELECTRICAL CHARACTERISTICS (PER LEG) (T_A=25°C unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I_R=0.50mA	200			V
Forward Voltage Drop	V_{FM}	I_F=1A, T_J=25°C		0.69		V
		I_F=1A, T_J=125°C		0.54		V
		I_F=3A, T_J=25°C		0.77		V
		I_F=3A, T_J=125°C		0.63		V
		I_F=5A, T_J=25°C		0.82	0.9	V
		I_F=5A, T_J=125°C		0.69	0.74	V
Leakage Current (Note 1)	I_{RM}	V_R=200V, T_J=25°C		2	100	μA
		V_R=200V, T_J=125°C		0.5	25	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.
2. Thermal resistance junction to case mounted on heatsink.